

ABSTRACT OF THE DISCLOSURE

A magnetic memory device includes a first
interconnection which runs in a first direction, a
second interconnection which runs in a second direction
5 different from the first direction, a magnetoresistive
element which is arranged at the intersection of and
between the first and second interconnections, and a
metal layer which is connected to the magnetoresistive
element and has a side surface that partially coincides
10 with a side surface of the magnetoresistive element.